MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G

Amplifier Transistors

NPN Silicon

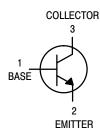
Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



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1 2

SOT-23 (TO-236) CASE 318 STYLE 6

MAXIMUM RATINGS

Rating	Symbol	6428LT1	6429LT1	Unit
Collector – Emitter Voltage	V_{CEO}	50	45	Vdc
Collector - Base Voltage	V_{CBO}	60 55		Vdc
Emitter – Base Voltage	V_{EBO}	6.0		Vdc
Collector Current – Continuous	I _C	200		mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Derate above 25 C		1.0	IIIVV/ C
Thermal Resistance, Junction–to–Ambient	$R_{ heta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C	P _D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.

MARKING DIAGRAM



XXX = Specific Device Code MMBT6428LT1 - 1KM NSV/MMBT6429LT1 - M1L

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT6428LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
MMBT6429LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
NSVMMBT6429LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS				•	•
Collector – Emitter Breakdown Voltage $(I_C = 1.0 \text{ mAdc}, I_B = 0)$ $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	MMBT6428 MMBT6429 / NSVMMBT6429	V _{(BR)CEO}	50 45	- -	Vdc
Collector – Base Breakdown Voltage ($I_C = 0.1 \text{ mAdc}, I_E = 0$) ($I_C = 0.1 \text{ mAdc}, I_E = 0$)	MMBT6428 MMBT6429 / NSVMMBT6429	V _{(BR)CBO}	60 55	- -	Vdc
Collector Cutoff Current (V _{CE} = 30 Vdc)		I _{CES}	_	0.1	μAdc
Collector Cutoff Current (V _{CB} = 30 Vdc, I _E = 0)		I _{CBO}	-	0.01	μAdc
Emitter Cutoff Current (V _{EB} = 5.0 Vdc, I _C = 0)		I _{EBO}	-	0.01	μAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 0.01 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$)	MMBT6428 MMBT6429 / NSVMMBT6429	h _{FE}	250 500	- -	-
$(I_C = 0.1 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT6428 MMBT6429 / NSVMMBT6429		250 500	650 1250	
$(I_C = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT6428 MMBT6429 / NSVMMBT6429		250 500	_ _	
$(I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT6428 MMBT6429 / NSVMMBT6429		250 500	- -	
Collector – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 0.5 \text{ mAdc}$) ($I_C = 100 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)		V _{CE(sat)}	_ _	0.2 0.6	Vdc
Base – Emitter On Voltage (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc)		V _{BE(on)}	0.56	0.66	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz)		f _T	100	700	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C_{obo}	_	3.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}	_	8.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

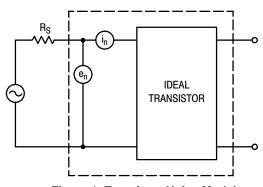


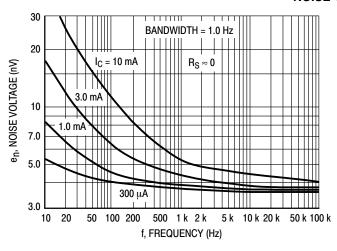
Figure 1. Transistor Noise Model

MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G

NOISE CHARACTERISTICS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$

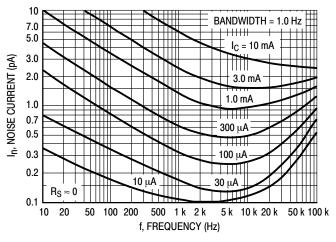
NOISE VOLTAGE



BANDWIDTH = 1.0 Hz 20 en, NOISE VOLTAGE (nV) $R_S \approx 0\,$ f = 10 Hz 10 100 Hz 7.0 1.0 kHz 5.0 3.0 0.01 0.02 0.05 0.1 0.2 0.5 1.0 5.0 10 IC, COLLECTOR CURRENT (mA)

Figure 2. Effects of Frequency

Figure 3. Effects of Collector Current



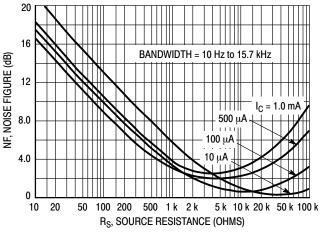
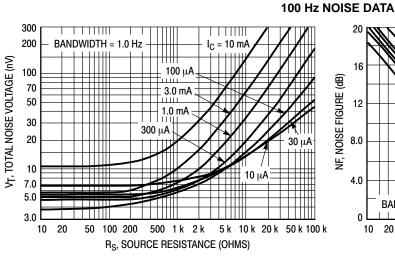


Figure 4. Noise Current

Figure 5. Wideband Noise Figure



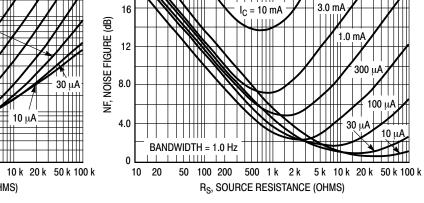


Figure 6. Total Noise Voltage

Figure 7. Noise Figure

MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G

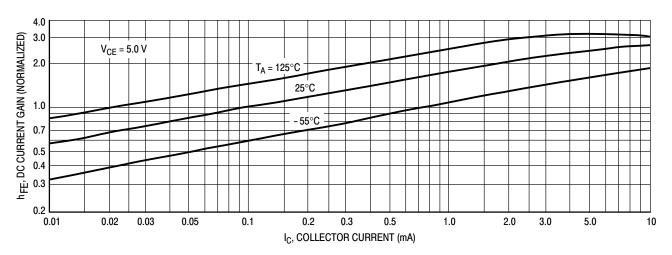


Figure 8. DC Current Gain

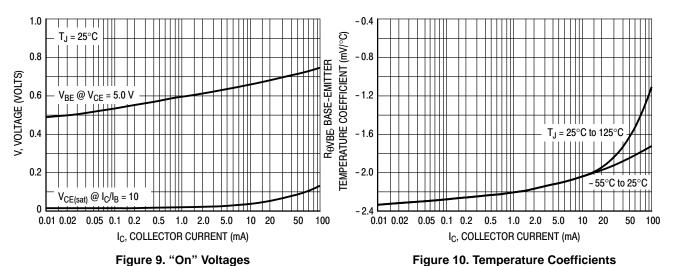


Figure 9. "On" Voltages

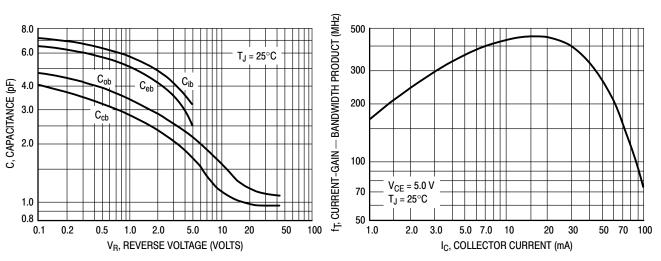


Figure 11. Capacitance

Figure 12. Current-Gain — Bandwidth Product

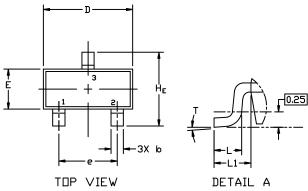




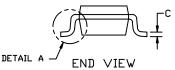
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DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10*



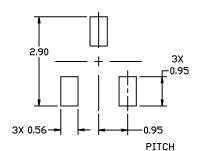


XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: I PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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